

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device structure, comprising:
 - a substrate defining a substantially horizontal plane;
 - a source region;
 - a drain region;
 - a gate electrode disposed on said substrate and being electrically insulated therefrom, said gate electrode positioned vertically between said source region and said drain region; and
 - at least one semiconducting nanotube including a first end electrically coupled with said source region, a second end electrically coupled with said drain region, and a channel region length extending vertically through said gate electrode between said first and second ends source region and said drain region, [[and]] said channel region being electrically insulated from said gate electrode, said gate electrode gating said length when a voltage is applied to said gate electrode to define a channel region for current flow from said source to said drain said channel region having a vertical dimension approximately equal to a length of said at least one semiconducting nanotube, and said gate electrode having a vertical dimension approximately equal to a length of said channel region of said at least one semiconducting nanotube.
 - 2. (Original) The semiconductor device structure of claim 1 wherein said source is composed of a catalyst material effective for growing said at least one semiconducting nanotube.
 - 3. (Previously Presented) The semiconductor device structure of claim 1 wherein said drain is composed of a catalyst material effective for growing said at least one semiconducting nanotube.

4. (Original) The semiconductor device structure of claim 1 further comprising:
an insulating layer disposed between said drain and said gate electrode for electrically isolating said drain from said gate electrode.

5. (Original) The semiconductor device structure of claim 1 further comprising:
an insulating layer disposed between said source and said gate electrode for electrically isolating said source from said gate electrode.

6. (Previously Presented) The semiconductor device structure of claim 1 wherein said at least one semiconducting nanotube is composed of arranged carbon atoms.

7. (Cancelled)

8. (Previously Presented) The semiconductor device structure of claim 1 wherein said at least one semiconducting nanotube is oriented substantially perpendicular to said horizontal plane.

9. (Previously Presented) The semiconductor device structure of claim 1 further comprising:
a plurality of semiconducting nanotubes extending vertically through said gate electrode.

10. (Previously Presented) The semiconductor device structure of claim 1 wherein said gate dielectric is disposed on said at least one semiconducting nanotube.

11-24. (Cancelled)

25. (Currently Amended) A semiconductor device structure, comprising:
a substrate;
an electrically-conductive first plate on said substrate,

an electrically-conductive second plate disposed vertically above said first plate; at least one nanotube having an end electrically coupled with said first plate ~~and a length that extends from said end vertically into said second plate for increasing an effective area of said first plate~~; and

~~a dielectric layer disposed between said second plate and said first plate, said dielectric layer coating said length of said at least one nanotube such that said at least one nanotube is electrically isolated from said second plate.~~

26. (Original) The semiconductor device structure of claim 25 wherein said at least one nanotube has a conducting molecular structure.

27. (Original) The semiconductor device structure of claim 25 wherein said at least one nanotube has a semiconducting molecular structure.

28. (Previously Presented) The semiconductor device structure of claim 25 wherein said dielectric layer encases said at least one nanotube.

29-33. (Cancelled)